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(71) Applicant (for all designated States except US): **KONINKLIJKE PHILIPS ELECTRONICS N.V.** [NL/NL];
Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **HUETING, Raymond, J., E.** [NL/NL]; c/o Philips Intellectual Property,

& Standards, Cross Oak Lane, Redhill Surrey RH1 5HA (GB). **HIJZEN, Erwin, A.** [NL/BE]; c/o Philips Intellectual Property, & Standards, Cross Oak Lane, Redhill Surrey RH1 5HA (GB).

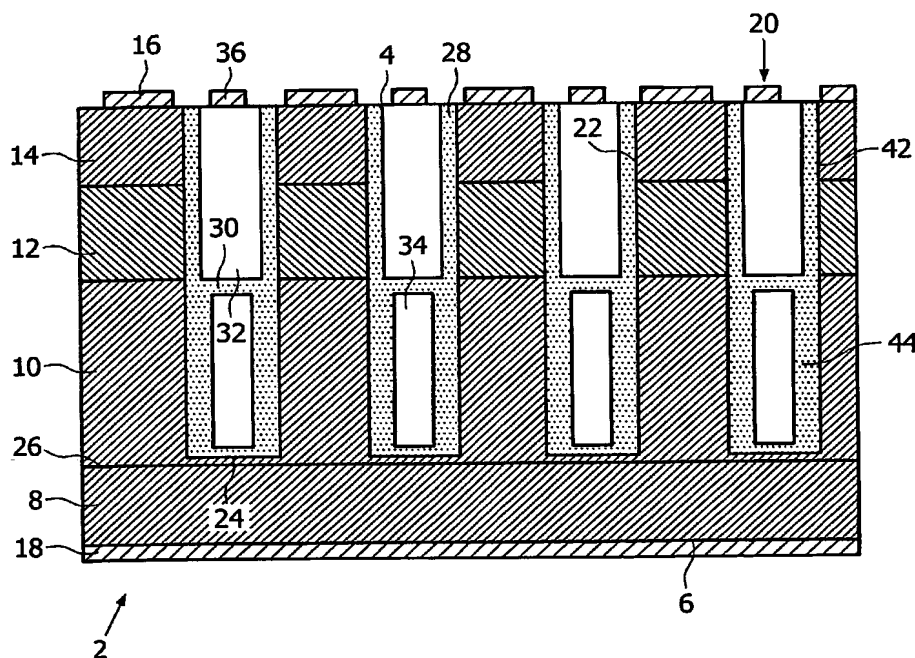
(74) Agents: **WILLIAMSON, Paul, L.** et al.; c/o Philips Intellectual Property, & Standards, Cross Oak Lane, Redhill Surrey RH1 5HA (GB).

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(54) Title: TRENCH INSULATED GATE FIELD EFFECT TRANSISTOR



(57) Abstract: The invention relates to a trench MOSFET with drain (8), drain region (10) body (12) and source (14). The drain region is doped to have a high concentration gradient. A field plate electrode (34) is provided adjacent to the sub-channel region (10) and a gate electrode (32) next to the body (12).



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